

# P-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)		
- 200	2.35 at V <sub>GS</sub> = - 10 V	- 0.49	8.0		
	2.45 at V <sub>GS</sub> = - 6.0 V	- 0.48	6.0		

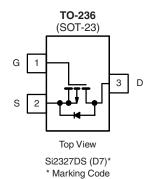
## **FEATURES**

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET<sup>®</sup> Power MOSFET
- Ultra Low On-Resistance
- Small Size



### **APPLICATIONS**

• Active Clamp Circuits in DC/DC Power Supplies



Ordering Information: Si2327DS -T1-E3 (Lead (Pb)-free)

Si2327DS -T1-GE3 (Lead (Pb)-free and Halogen-free)

Parameter	Symbol	5 s	Steady State	Unit		
Drain-Source Voltage		V <sub>DS</sub>	- 200		V	
Gate-Source Voltage		V <sub>GS</sub>	± 20			
Continuous Dusin Comment /T 150 °C\3 b	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 0.49	- 0.38		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a, b</sup>	T <sub>A</sub> = 70 °C		- 0.39	- 0.31		
Pulsed Drain Current		I <sub>DM</sub>	- 1.0		Α	
Continuous Source Current (Diode Conduction) <sup>a, b</sup>		I <sub>S</sub>	- 1.0	- 0.6		
Single Pulse Avalanche Current	L = 1.0 mH	I <sub>AS</sub>	4.0 0.8			
Single Pulse Avalanche Energy	L = 1.0 MH	E <sub>AS</sub>			mJ	
Mariana Bana Biratantan h	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.25	0.75	W	
Maximum Power Dissipation <sup>a, b</sup>	T <sub>A</sub> = 70 °C		0.8	0.48	"	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marrian II washing to Amshingta	t ≤ 5 s	R <sub>thJA</sub>	75	100	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	' 'thJA	120	166		
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	40	50		

## Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.

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SPECIFICATIONS T <sub>J</sub> = 25 °C	C, unless o	otherwise noted					
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 200			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$	- 2.5		- 4.5	\ \ \	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zara Cata Valtaga Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 200 V, V <sub>GS</sub> = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current		$V_{DS} = -200 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le$ - 15 V, $V_{GS}$ = 10 V	- 1.0			Α	
D : 0	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 0.5 A		1.9	2.35	Ω	
Drain-Source On-Resistance <sup>a</sup>		$V_{GS} = -6.0 \text{ V}, I_D = -0.5 \text{ A}$		1.96	2.45		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 0.5 A		1.8		S	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> = - 1.0 A, V <sub>GS</sub> = 0 V		- 0.85	- 1.2	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$	V - 100 V V - 10 V		8.0	12	nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -100 \text{ V}, V_{GS} = 10 \text{ V}$ $I_{D} \cong -0.5 \text{ A}$		1.3			
Gate-Drain Charge	$Q_{gd}$	ID = 0.5 /\		2.5			
Gate Resistance	$R_{g}$	f = 1.0 MHz		8.0		Ω	
Input Capacitance	C <sub>iss</sub>			340	510		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		25		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			14			
Switching <sup>c</sup>				•			
Turn-On Time	t <sub>d(on)</sub>	$V_{DD} = -100 \text{ V}, R_L = 100 \Omega$ $I_D \cong -1.0 \text{ A}, V_{GEN} = -10 \text{ V}$		8	12	ns	
ium-on time	t <sub>r</sub>			11	17		
Turn-Off Time	t <sub>d(off)</sub>	$R_{a} = 6 \Omega$		16	25	113	
Tutti-Oil Tillie	t <sub>f</sub>			11	17		
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = 0.5 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$		140	200	nC	

### Notes:

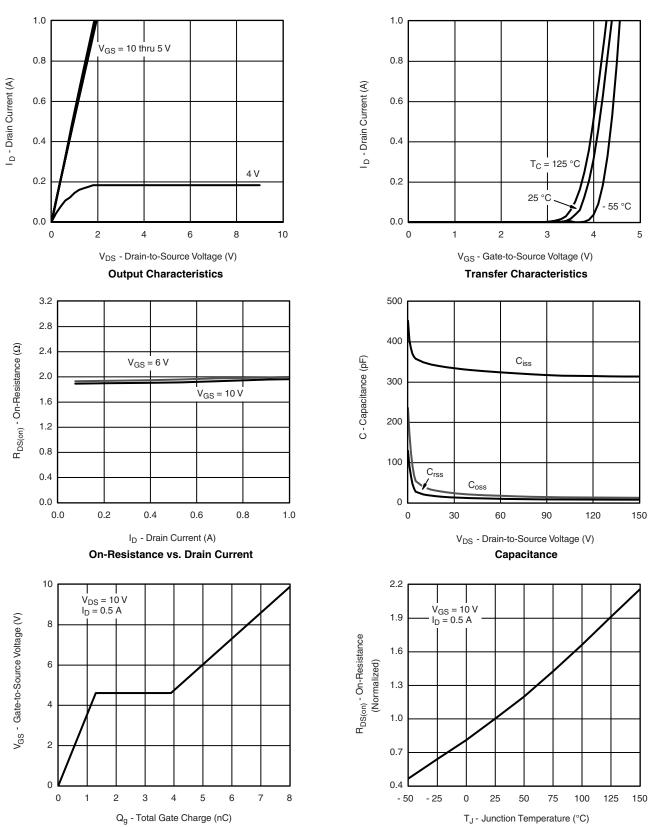
- a. Pulse test: PW  $\leq$  300  $\mu s$  duty cycle  $\leq$  2 %.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



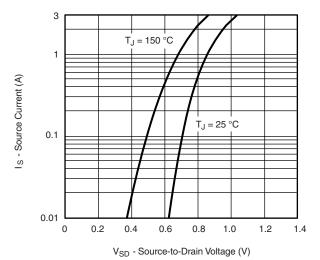
**Gate Charge** 

On-Resistance vs. Junction Temperature

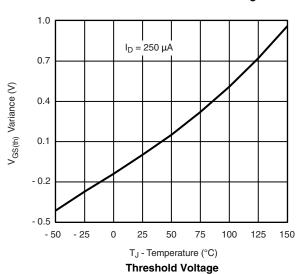
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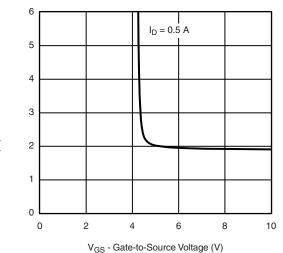
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



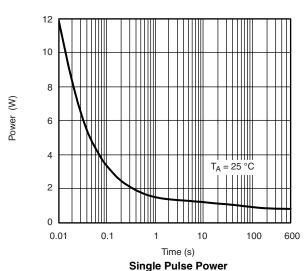
Source-Drain Diode Forward Voltage

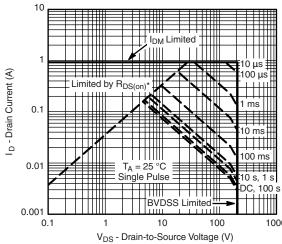


 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - On-Resistance  $(\Omega)$ 



On-Resistance vs. Gate-to-Source Voltage



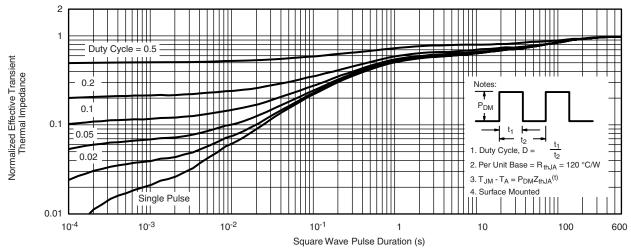


\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?73240">www.vishay.com/ppg?73240</a>.

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